Dual 1-of-4 Decoder/ Demultiplexer

High-Performance Silicon-Gate CMOS

The MC74HC139A is identical in pinout to the LS139. The device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs.

This device consists of two independent 1-of-4 decoders, each of which decodes a two-bit Address to one-of-four active-low outputs. Active-low Selects are provided to facilitate the demultiplexing and cascading functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output, and utilizing the Select as a data input.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 100 FETs or 25 Equivalent Gates
- Pb-Free Packages are Available*



ON Semiconductor®

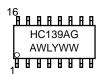
http://onsemi.com

MARKING DIAGRAMS



PDIP-16 N SUFFIX CASE 648 

SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F





SOEIAJ-16 F SUFFIX CASE 966



A = Assembly Location

L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb-Free Package
= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

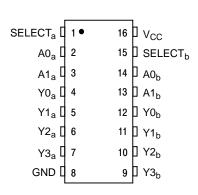


Figure 1. Pin Assignment

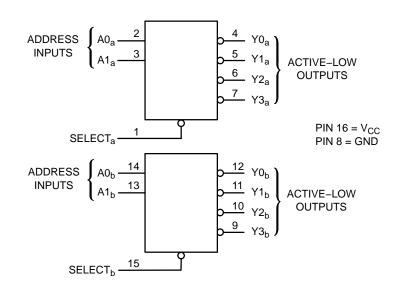


Figure 2. Logic Diagram

FUNCTION TABLE

Inputs				Out	puts	
Select	A1	Α0	Y0	Y1	Y2	Y3
Н	Х	Χ	Н	Н	Н	Н
L	L	L	L	Н	Н	Н
L	L	Н	Н	L	Н	Н
L	Н	L	Н	Н	L	Н
L	Н	Н	Н	Н	Н	L

X = don't care

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC139AN	PDIP-16	2000 Units / Box
MC74HC139ANG	PDIP-16 (Pb-Free)	2000 Units / Box
MC74HC139AD	SOIC-16	48 Units / Rail
MC74HC139ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC139ADR2	SOIC-16	2500 Units / Reel
MC74HC139ADR2G	SOIC-16 (Pb-Free)	2500 Units / Reel
MC74HC139ADTR2	TSSOP-16*	2500 Units / Reel
MC74HC139ADTR2G	TSSOP-16*	2500 Units / Reel
MC74HC139AFEL	SOEIAJ-16	2000 Units / Reel
MC74HC139AFELG	SOEIAJ-16 (Pb-Free)	2000 Units / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

MAXIMUM RATINGS

Symbol	Param	eter	Value	Unit
V _{CC}	DC Supply Voltage	(Referenced to GND)	-0.5 to +7.0	V
V _{IN}	DC Input Voltage	(Referenced to GND)	-1.5 to V _{CC} +1.5	V
V _{OUT}	DC Output Voltage	(Referenced to GND) (Note 1)	-0.5 to V_{CC} + 0.5	V
I _{IN}	DC Input Current, per Pin		±20	mA
I _{OUT}	DC Output Current, per Pin		±25	mA
I _{CC}	DC Supply Current, V _{CC} Pin		± 50	mA
I _{GND}	DC Ground Current per Ground Pin		±50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 1	0 Seconds	260	°C
T_J	Junction Temperature Under Bias		+ 150	°C
$\theta_{\sf JA}$	Thermal Resistance	PDIP SOIC TSSOP	78 112 148	°C/W
P _D	Power Dissipation in Still Air at 85°C	PDIP SOIC TSSOP	750 500 450	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% - 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 > 1000	V
I _{LATCHUP}	Latchup Performance Above	V _{CC} and Below GND at 85°C (Note 5)	±300	mA

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- I_O absolute maximum rating must be observed.
 Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- Tested to EIA/JESD78.
- 6. For high frequency or heavy load considerations, see Chapter 2the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage	(Referenced to GND)	2.0	6.0	V
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage	(Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types		- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 3)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

7. Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			V _{CC} Guaranteed Limit				
Symbol	Parameter	Test Conditions	٧	−55°C to 25°C	≤ 85 ° C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	V_{OUT} = 0.1 V or V_{CC} -0.1 V $ I_{OUT} \le 20 \mu A$	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V _{IL}	Maximum Low–Level Input Voltage	V_{OUT} = 0.1 V or V_{CC} -0.1 V $ I_{OUT} \le 20 \mu A$	2.0 4.5 6.0	0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{IN} = V_{IH} \text{ or } V_{IL} \qquad \begin{vmatrix} I_{OUT} \end{vmatrix} \le 4.0 \text{ mA} \\ I_{OUT} \le 5.2 \text{ mA} \end{vmatrix}$	4.5 6.0	3.98 5.48	3.84 5.34	3.70 5.20	
V _{OL}	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	٧
		$V_{IN} = V_{IH} \text{ or } V_{IL} \qquad \begin{vmatrix} I_{OUT} \end{vmatrix} \le 4.0 \text{ mA} \\ I_{OUT} \le 5.2 \text{ mA} \end{vmatrix}$	4.5 6.0	0.26 0.26	0.33 0.33	0.40 0.40	
I _{IN}	Maximum Input Leakage Current	V _{IN} = V _{CC} or GND	6.0	±0.1	± 1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0	4	40	160	μΑ

^{8.} Information on typical parametric values can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6.0 \text{ ns}$)

		V _{CC}	Guaranteed Limit			
Symbol	Parameter	٧	−55°C to 25°C	≤ 85°C	≤125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Select to Output Y (Figures 1 and 3)	2.0 4.5 6.0	115 23 20	145 29 25	175 35 30	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 2 and 3)	2.0 4.5 6.0	115 23 20	145 29 25	175 35 30	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF

^{9.} For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Decoder) (Note 10)	55	pF

^{10.} Used to determine the no-load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

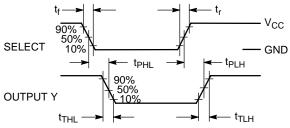


Figure 3. Switching Waveform

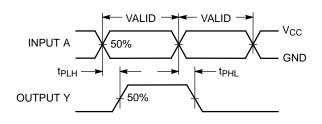
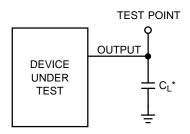


Figure 4. Switching Waveform



^{*} Includes all probe and jig capacitance

Figure 5. Test Circuit

PIN DESCRIPTIONS

ADDRESS INPUTS

A0_a, A1_a, A0_b, A1_b (Pins 2, 3, 14, 13)

Address inputs. These inputs, when the respective 1–of–4 decoder is enabled, determine which of its four active–low outputs is selected.

CONTROL INPUTS

Select_a, Select_b (Pins 1, 15)

Active—low select inputs. For a low level on this input, the outputs for that particular decoder follow the Address

inputs. A high level on this input forces all outputs to a high level

OUTPUTS

$$Y0_a - Y3_a$$
, $Y0_b - Y3_b$ (Pins 4 – 7, 12, 11, 10, 9)

Active—low outputs. These outputs assume a low level when addressed and the appropriate Select input is active. These outputs remain high when not addressed or the appropriate Select input is inactive.

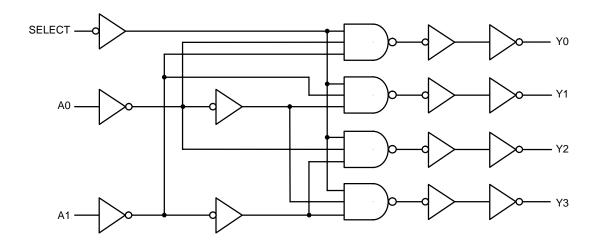
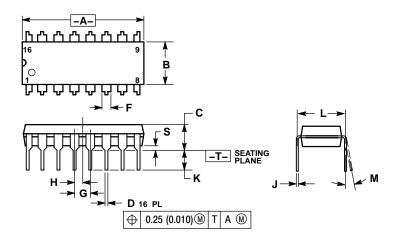


Figure 6. Expanded Logic Diagram (1/2 of Device)

PACKAGE DIMENSIONS

PDIP-16 **N SUFFIX** CASE 648-08 **ISSUE T**

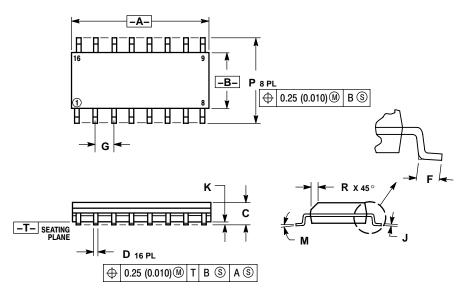


NOTES:

- DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING F ANSI 714.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 DIMENSION B DOES NOT INCLUDE MOLD FLASH.
- 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100	BSC	2.54	BSC
Н	0.050 BSC		1.27	BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10 °	0°	10 °
S	0.020	0.040	0.51	1.01

SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

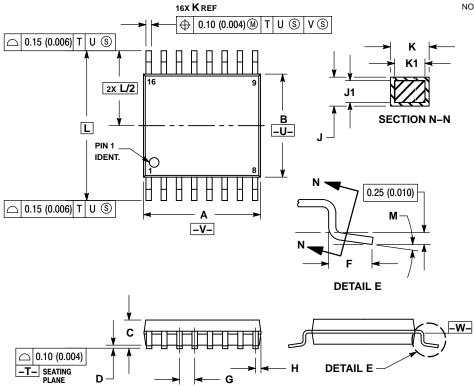
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIGN.

- MAXIMUM MOLD PHOLICISION 0.15 (0.006)
 PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE A**



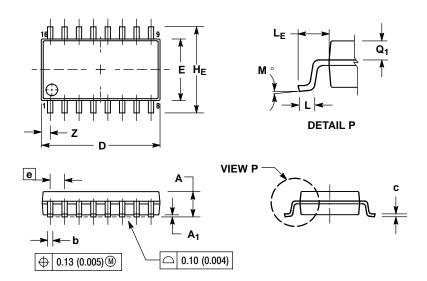
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K

 - (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL
 - 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	0.65 BSC		BSC
Н	0.18	0.28	0.007	0.011
۲	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252 BSC	
M	0°	8°	0°	8 °

PACKAGE DIMENSIONS

SOEIAJ-16 **F SUFFIX** CASE 966-01 **ISSUE O**



NOTES:

- 11-5.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (n ona) DER SIDE
- OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q	0.70	0.90	0.028	0.035
Z		0.78		0.031

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